

IGBT - Power, Single, N-Channel, Field Stop VII (FS7), SCR, Power TO247-4L

1200 V, 1.37 V, 25 A

AFGH4L25T120RW

Description

Using the novel field stop 7th generation IGBT technology in TO247 4-lead package, this device offers the optimum performance with low on state voltage and minimal switching losses for both hard and soft switching topologies in automotive applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Maximum Junction Temperature – $T_J = 175^\circ\text{C}$
- Short Circuit Rated and Low Saturation Voltage
- Fast Switching and Tightened Parameter Distribution
- AEC-Q101 Qualified, PPAP Available Upon Request
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

- Automotive E-compressor
- Automotive EV PTC Heater
- OBC

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

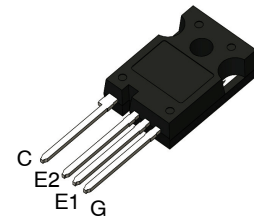
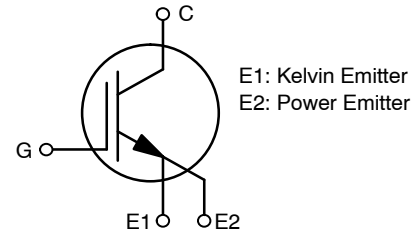
| Parameter | Symbol | Value | Unit |
|--------------------------------------------------------------------------------------------------------|----------------|---------------------------|------------------|
| Collector-to-Emitter Voltage | V_{CE} | 1200 | V |
| Gate-to-Emitter Voltage | V_{GE} | ± 20 | V |
| Transient Gate-to-Emitter Voltage | | ± 30 | |
| Collector Current | I_C | $T_C = 25^\circ\text{C}$ | A |
| | | $T_C = 100^\circ\text{C}$ | |
| Power Dissipation | P_D | $T_C = 25^\circ\text{C}$ | W |
| | | $T_C = 100^\circ\text{C}$ | |
| Pulsed Collector Current | I_{CM} | 75 | A |
| Short Circuit Withstand Time $V_{GE} = 15\text{ V}, V_{CC} = 800\text{ V}, T_C = 150^\circ\text{C}$ | T_{SC} | 6 | μs |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +175 | $^\circ\text{C}$ |
| Lead Temperature for Soldering Purposes | T_L | 260 | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating; Pulse width limited by max. junction temperature

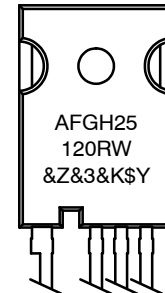
| BV_{CES} | $V_{CE(sat)}$ TYP | I_C MAX |
|------------|-------------------|-----------|
| 1200 V | 1.37 V | 25 A |

PIN CONNECTIONS



TO-247-4LD
CASE 340CJ

MARKING DIAGRAM



AFGH25120RW = Specific Device Code
&Z = Assembly Plant Code
&3 = 3-Digit Date Code
&K = 2-Digit Lot Traceability Code
\$Y = onsemi Logo

ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|---------------------|-----------------|
| AFGH4L25T120RW | TO-247-4L (Pb-Free) | 30 Units / Rail |

AFGH4L25T120RW

THERMAL CHARACTERISTICS

| Parameter | Symbol | Value | Unit |
|-----------------------------------------------|-----------------|-------|------|
| Thermal Resistance, Junction-to-Case for IGBT | $R_{\theta JC}$ | 0.42 | °C/W |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 40 | |

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------|--------|-----------------|-----|-----|-----|------|
|-----------|--------|-----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|----------------------------------------|------------|-------------------------------------------------|------|---|-----------|---------------|
| Collector-to-Emitter Breakdown Voltage | BV_{CES} | $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$ | 1200 | - | - | V |
| Zero Gate Voltage Collector Current | I_{CES} | $V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$ | - | - | 40 | μA |
| Gate-to-Emitter Leakage Current | I_{GES} | $V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$ | - | - | ± 400 | nA |

ON CHARACTERISTICS

| | | | | | | |
|-----------------------------------------|---------------|--------------------------------------------------------------------|------|------|------|---|
| Gate-to-Emitter Threshold Voltage | $V_{GE(th)}$ | $V_{GE} = V_{CE}, I_C = 25\text{ mA}$ | 5.03 | 5.93 | 6.83 | V |
| Collector-to-Emitter Saturation Voltage | $V_{CE(sat)}$ | $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 25^\circ\text{C}$ | - | 1.37 | 1.70 | V |
| | | $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 175^\circ\text{C}$ | - | 1.62 | - | |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|------------------------------|-----------|------------------------------------------------------------------|---|------|---|---------------|
| Input Capacitance | C_{IES} | $V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | - | 3058 | - | μF |
| Output Capacitance | C_{OES} | | - | 94.3 | - | |
| Reverse Transfer Capacitance | C_{RES} | | - | 15.8 | - | |
| Total Gate Charge | Q_G | $V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 25\text{ A}$ | - | 113 | - | nC |
| Gate-to-Emitter Charge | Q_{GE} | | - | 27.2 | - | |
| Gate-to-Collector Charge | Q_{GC} | | - | 49.9 | - | |

SWITCHING CHARACTERISTICS (Note: Si Diode Applied)

| | | | | | | |
|-------------------------|--------------|---------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------|------|------|----|
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 12.5\text{ A}, R_G = 8\ \Omega, T_J = 25^\circ\text{C}$ | - | 39.7 | - | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 254 | - | |
| Rise Time | t_r | | - | 19.3 | - | |
| Fall Time | t_f | | - | 192 | - | |
| Turn-On Switching Loss | E_{on} | | - | 0.52 | - | mJ |
| Turn-Off Switching Loss | E_{off} | | - | 0.86 | - | |
| Total Switching Loss | E_{ts} | | - | 1.38 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | | $V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 25\text{ A}, R_G = 8\ \Omega, T_J = 25^\circ\text{C}$ | - | 43 | |
| Turn-Off Delay Time | $t_{d(off)}$ | - | | 203 | - | |
| Rise Time | t_r | - | | 32.7 | - | |
| Fall Time | t_f | - | | 126 | - | |
| Turn-On Switching Loss | E_{on} | | - | 1.46 | - | mJ |
| Turn-Off Switching Loss | E_{off} | | - | 1.07 | - | |
| Total Switching Loss | E_{ts} | | - | 2.53 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | | $V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 12.5\text{ A}, R_G = 8\ \Omega, T_J = 175^\circ\text{C}$ | - | 42.5 | |
| Turn-Off Delay Time | $t_{d(off)}$ | - | | 348 | - | |
| Rise Time | t_r | - | | 27.4 | - | |
| Fall Time | t_f | - | | 384 | - | |
| Turn-On Switching Loss | E_{on} | | - | 0.75 | - | mJ |
| Turn-Off Switching Loss | E_{off} | | - | 1.61 | - | |
| Total Switching Loss | E_{ts} | | - | 2.36 | - | |

AFGH4L25T120RW

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------------------------------------------------------|--------------|------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| SWITCHING CHARACTERISTICS (Note: Si Diode Applied) | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $I_C = 25\text{ A}, R_G = 8\ \Omega,$ $T_J = 175^\circ\text{C}$ | - | 47.3 | - | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 265 | - | |
| Rise Time | t_r | | - | 45 | - | |
| Fall Time | t_f | | - | 241 | - | |
| Turn-On Switching Loss | E_{on} | | - | 2.15 | - | mJ |
| Turn-Off Switching Loss | E_{off} | | - | 1.92 | - | |
| Total Switching Loss | E_{ts} | | - | 4.07 | - | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AFGH4L25T120RW

TYPICAL CHARACTERISTICS

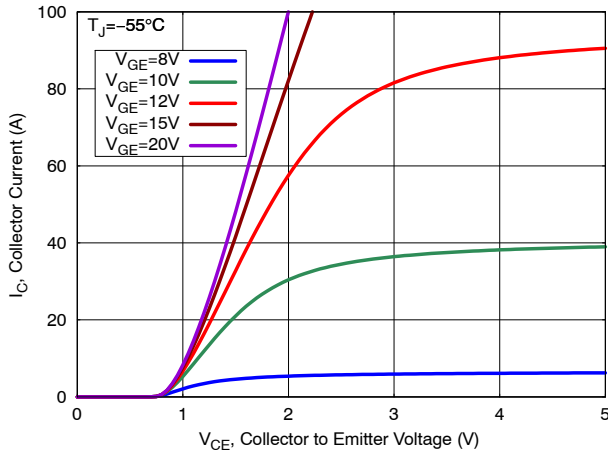


Figure 1. Output Characteristics

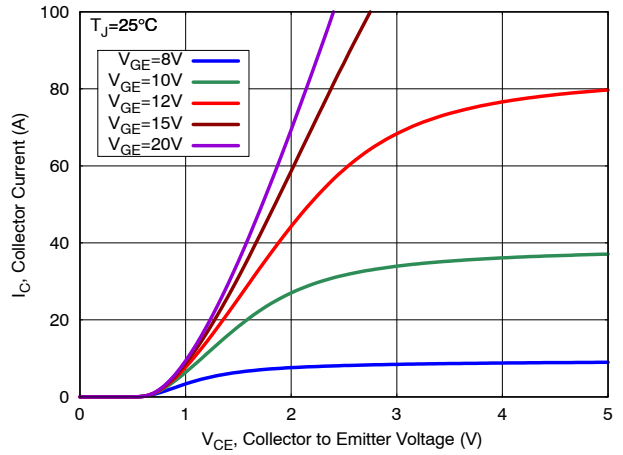


Figure 2. Output Characteristics

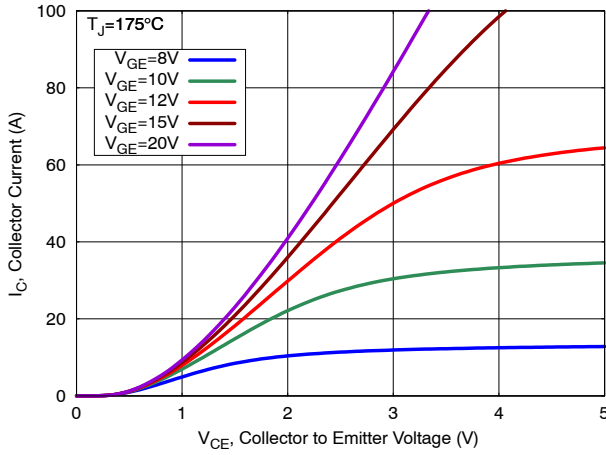


Figure 3. Output Characteristics

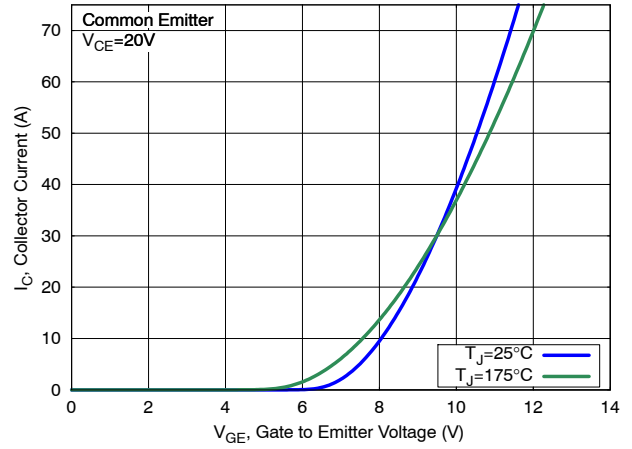


Figure 4. Transfer Characteristics

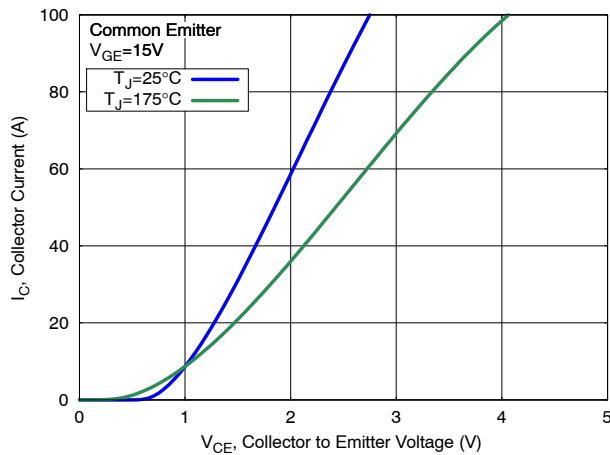


Figure 5. Saturation Characteristics

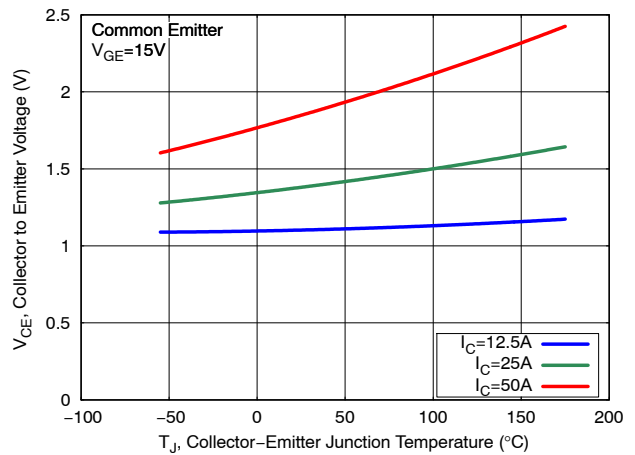


Figure 6. Saturation Voltage vs. Junction Temperature

AFGH4L25T120RW

TYPICAL CHARACTERISTICS

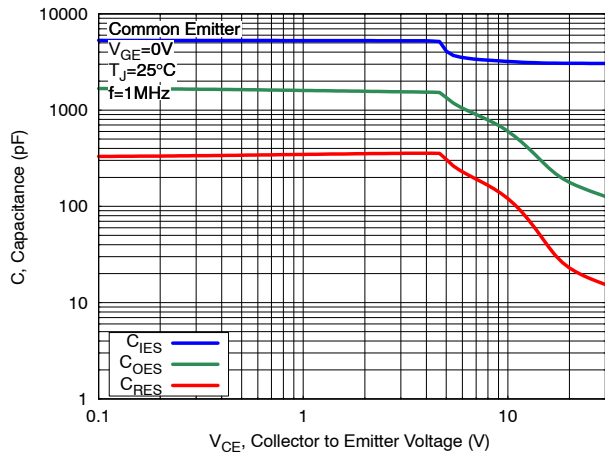


Figure 7. Capacitance Characteristics

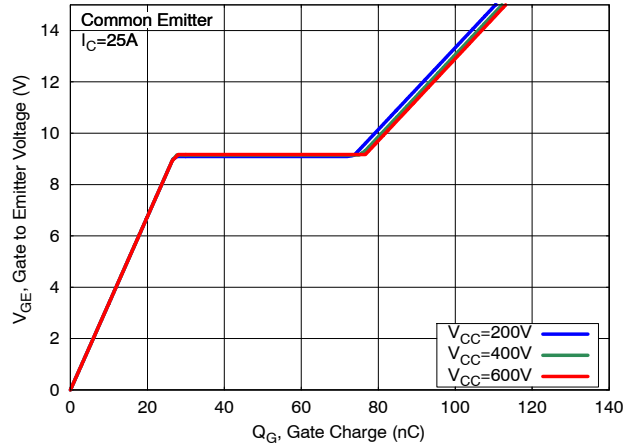


Figure 8. Gate Charge Characteristics

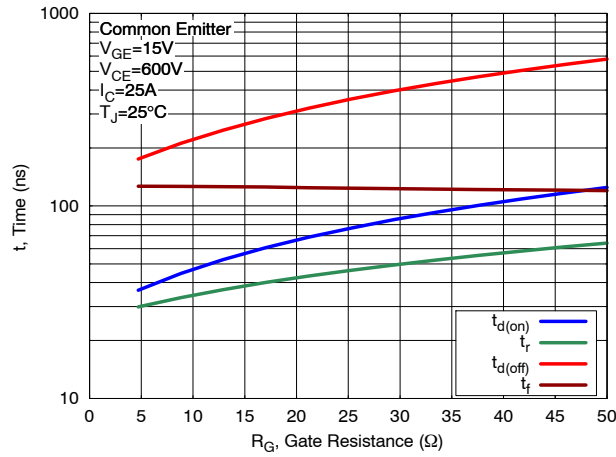


Figure 9. Switching Time vs Gate Resistance

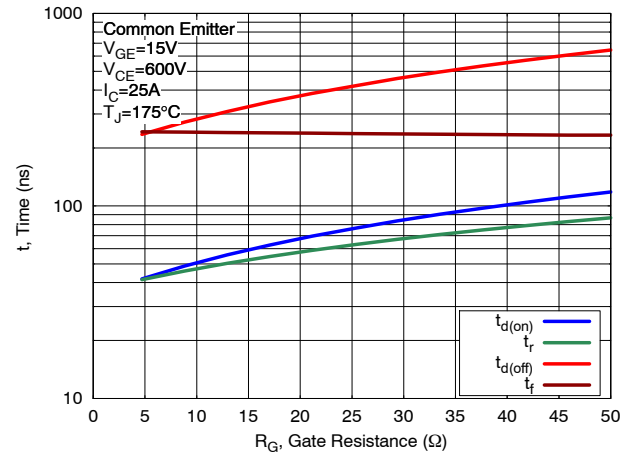


Figure 10. Switching Time vs Gate Resistance

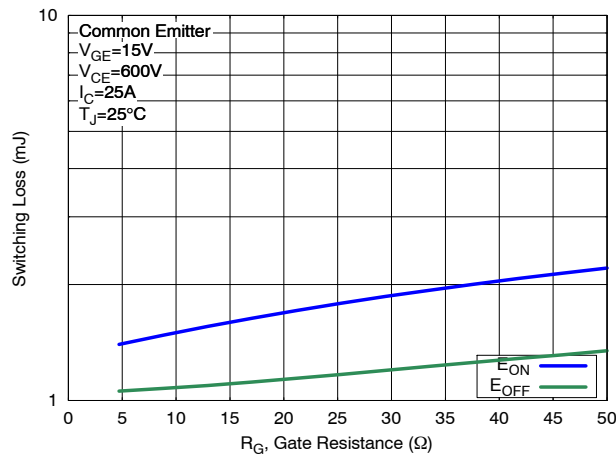


Figure 11. Switching Loss vs Gate Resistance

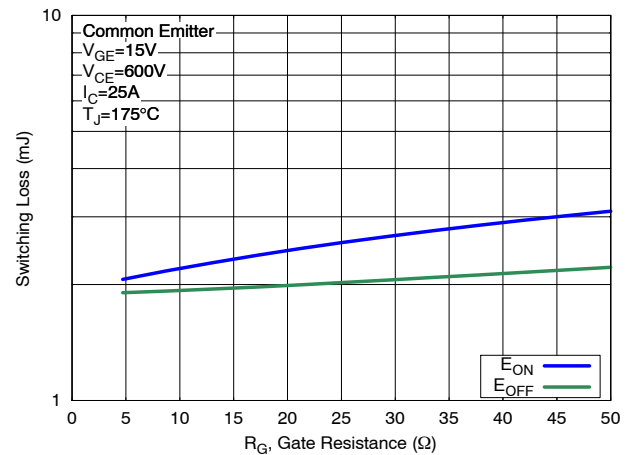


Figure 12. Switching Loss vs Gate Resistance

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TYPICAL CHARACTERISTICS

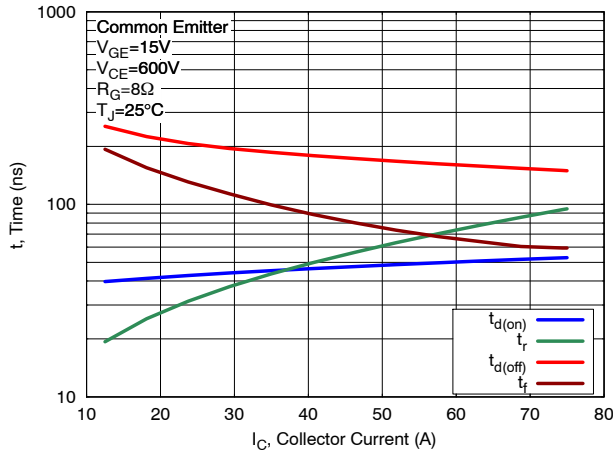


Figure 13. Switching Time vs Collector Current

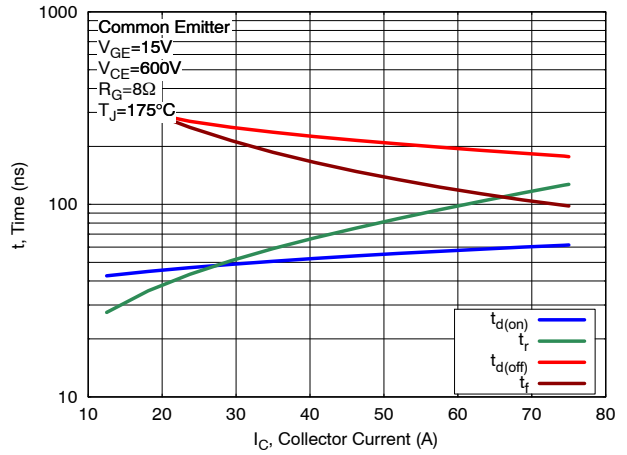


Figure 14. Switching Time vs Collector Current

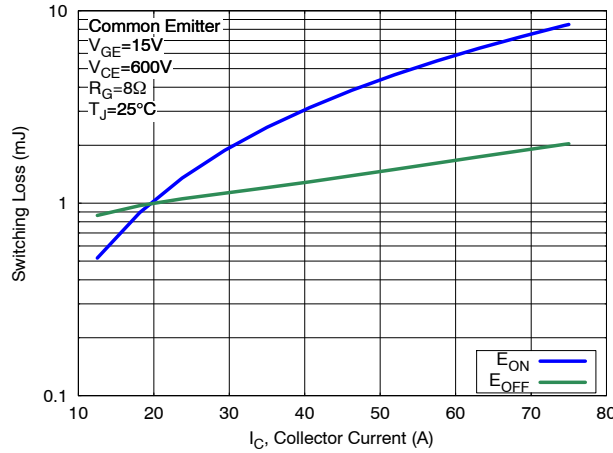


Figure 15. Switching Loss vs Collector Current

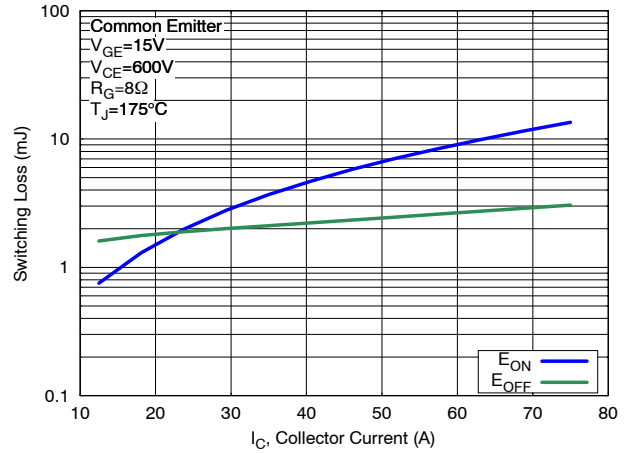


Figure 16. Switching Loss vs Collector Current

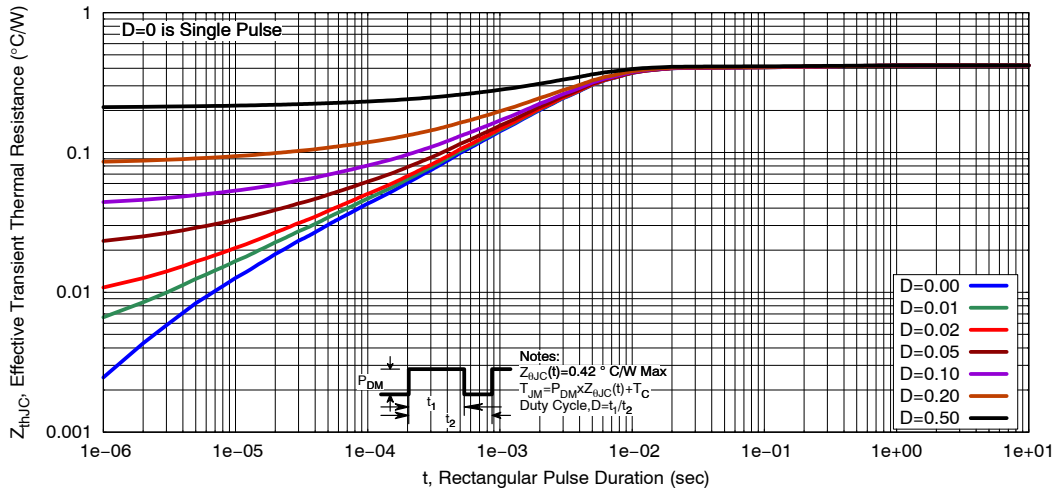


Figure 17. Transient Thermal Impedance of IGBT

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019



| DIM | MILLIMETERS | | |
|-----|-------------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.80 | 5.00 | 5.20 |
| A1 | 2.10 | 2.40 | 2.70 |
| A2 | 1.80 | 2.00 | 2.20 |
| b | 1.07 | 1.20 | 1.33 |
| b1 | 1.20 | 1.40 | 1.60 |
| b2 | 2.02 | 2.22 | 2.42 |
| c | 0.50 | 0.60 | 0.70 |
| D | 22.34 | 22.54 | 22.74 |
| D1 | 16.00 | 16.25 | 16.50 |
| D2 | 0.97 | 1.17 | 1.37 |
| e | 2.54 BSC | | |
| e1 | 5.08 BSC | | |
| E | 15.40 | 15.60 | 15.80 |
| E1 | 12.80 | 13.00 | 13.20 |
| E/2 | 4.80 | 5.00 | 5.20 |
| L | 18.22 | 18.42 | 18.62 |
| L1 | 2.42 | 2.62 | 2.82 |
| p | 3.40 | 3.60 | 3.80 |
| p1 | 6.60 | 6.80 | 7.00 |
| Q | 5.97 | 6.17 | 6.37 |
| S | 5.97 | 6.17 | 6.37 |

NOTES:

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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

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